

Fig. 1

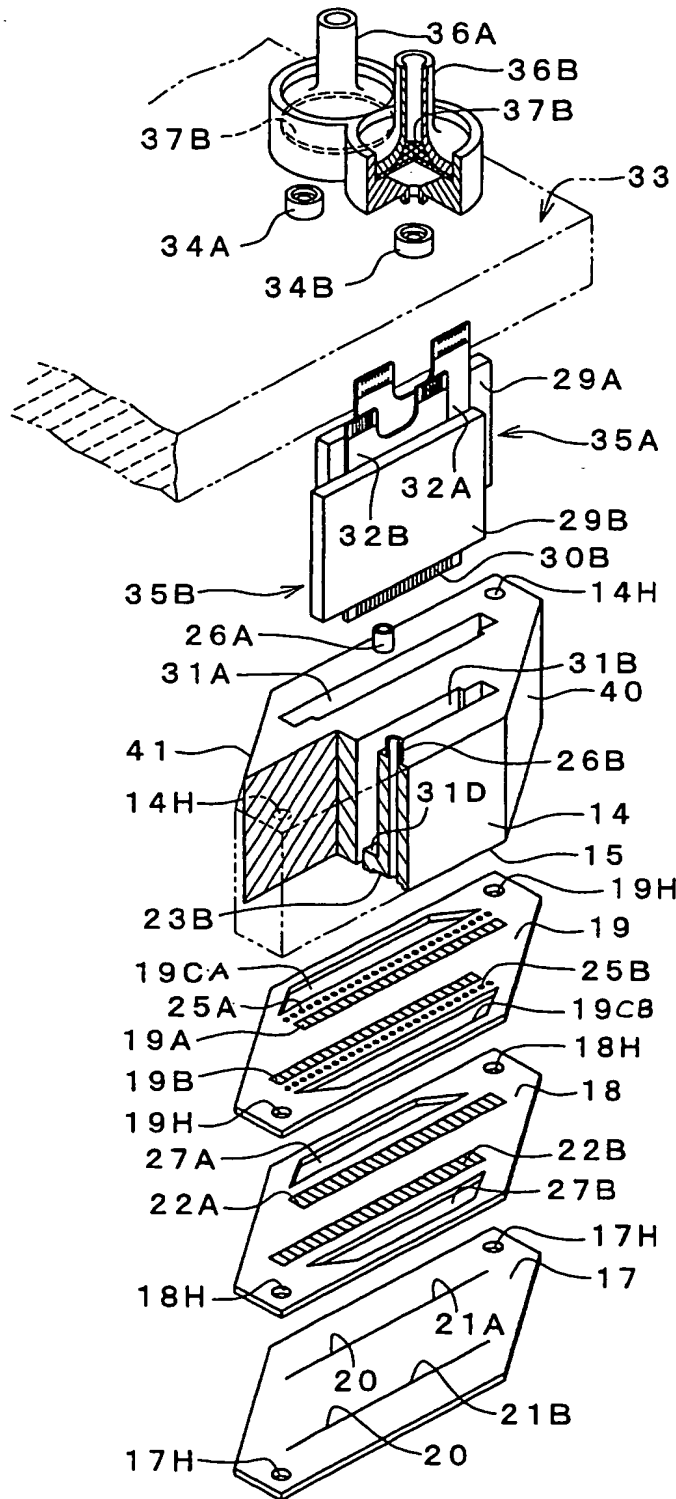
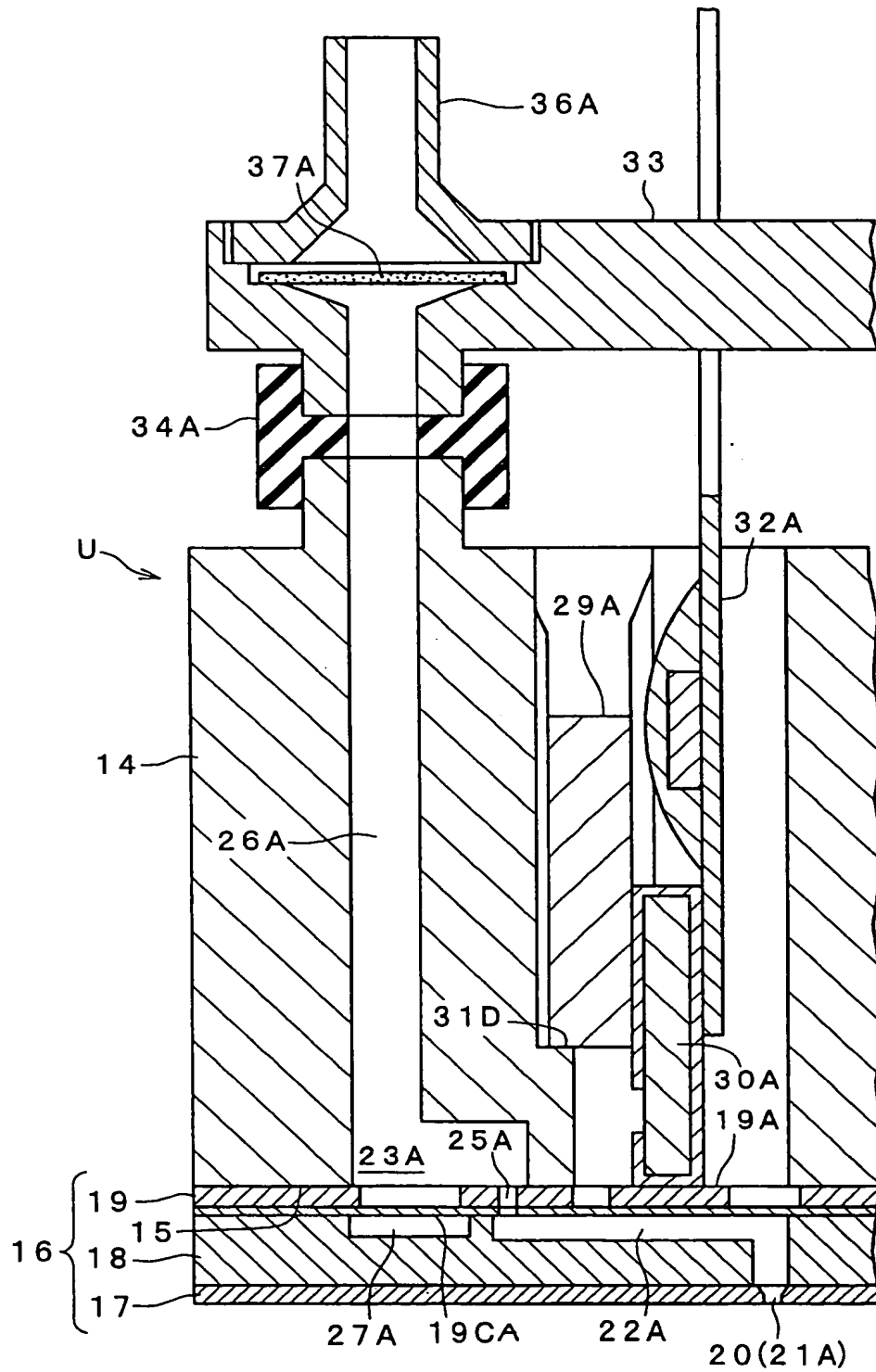


Fig. 2



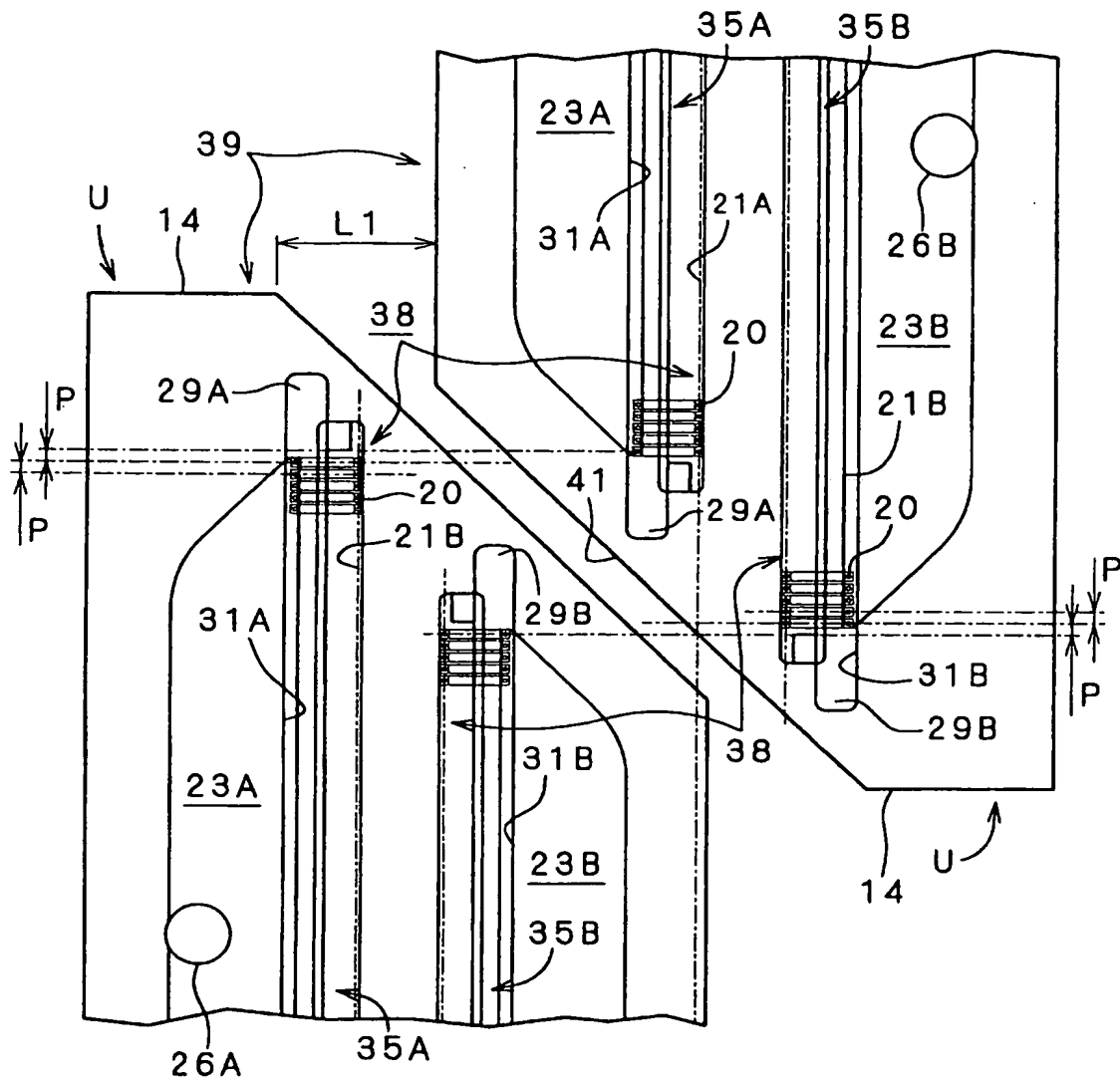


Fig. 3

Fig. 4A

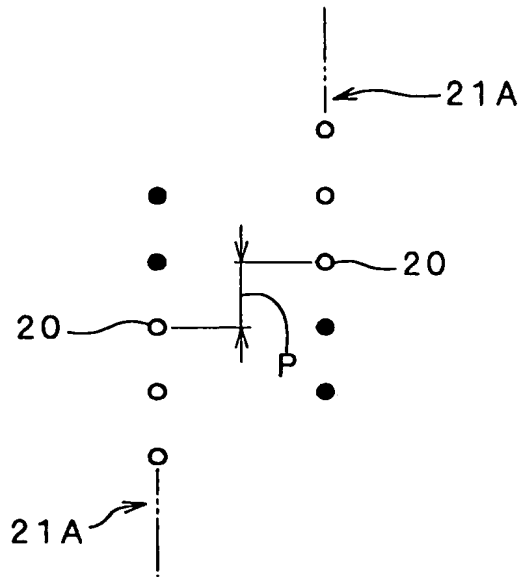
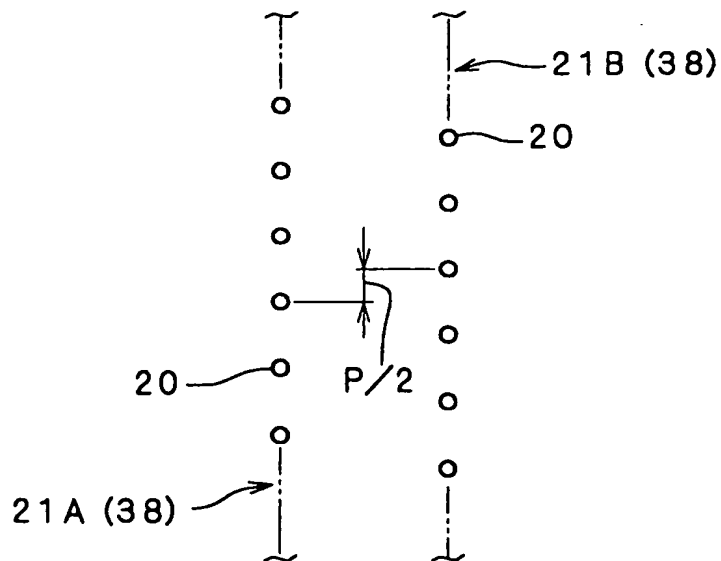


Fig. 4B



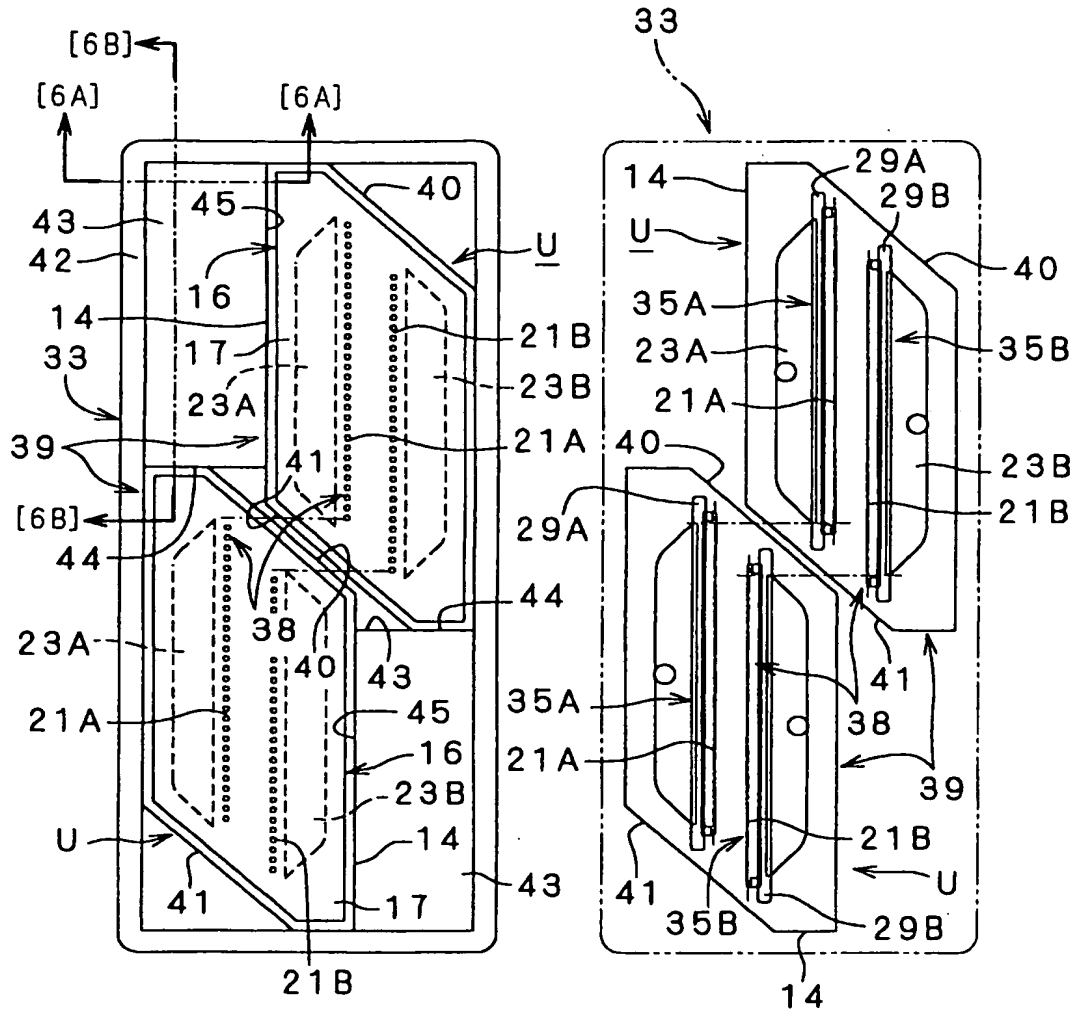


Fig. 5A

Fig. 5B

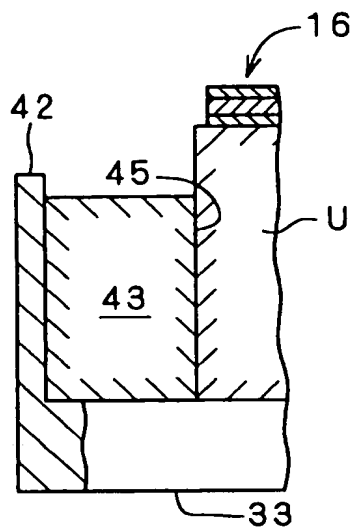


Fig. 6A

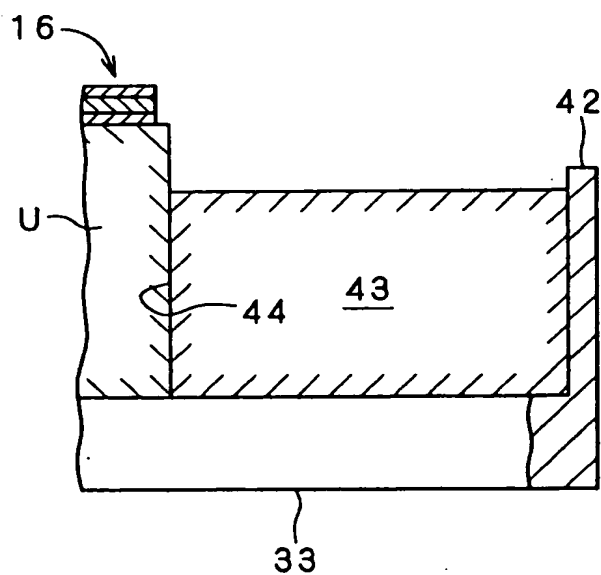


Fig. 6B

Fig. 7A

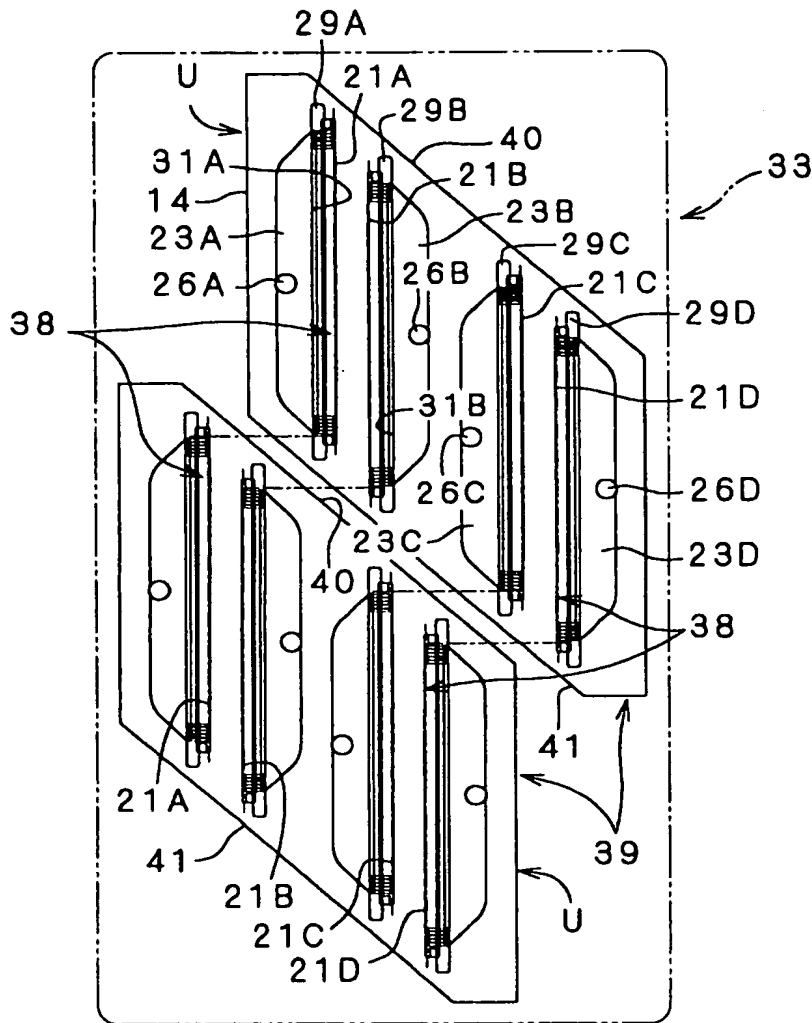
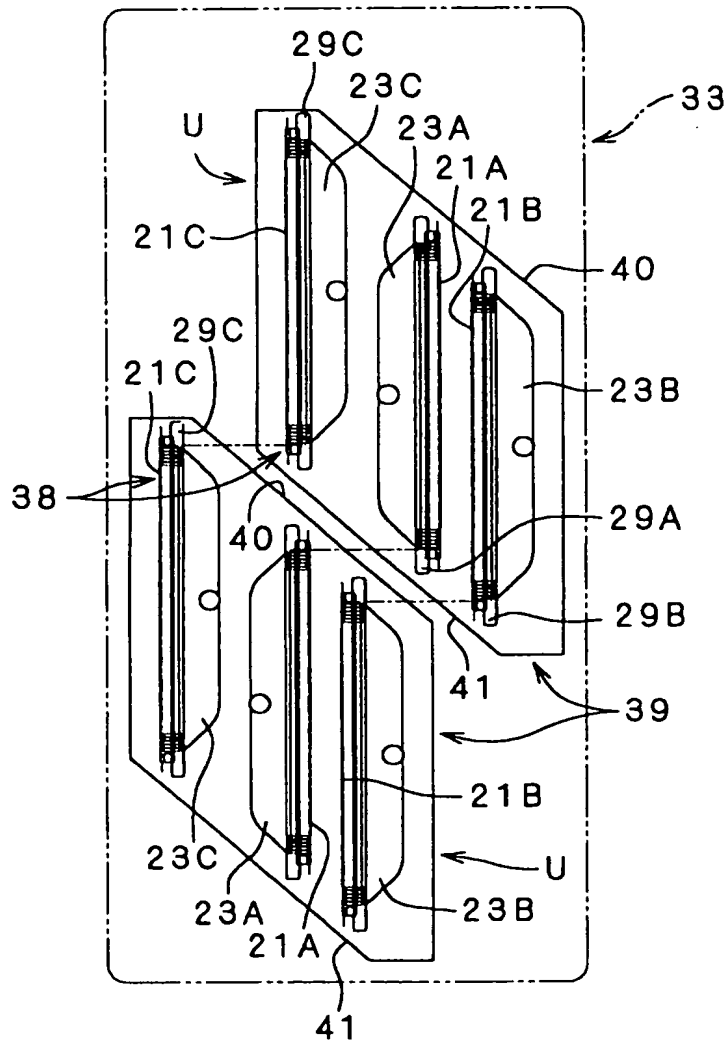


Fig. 7B



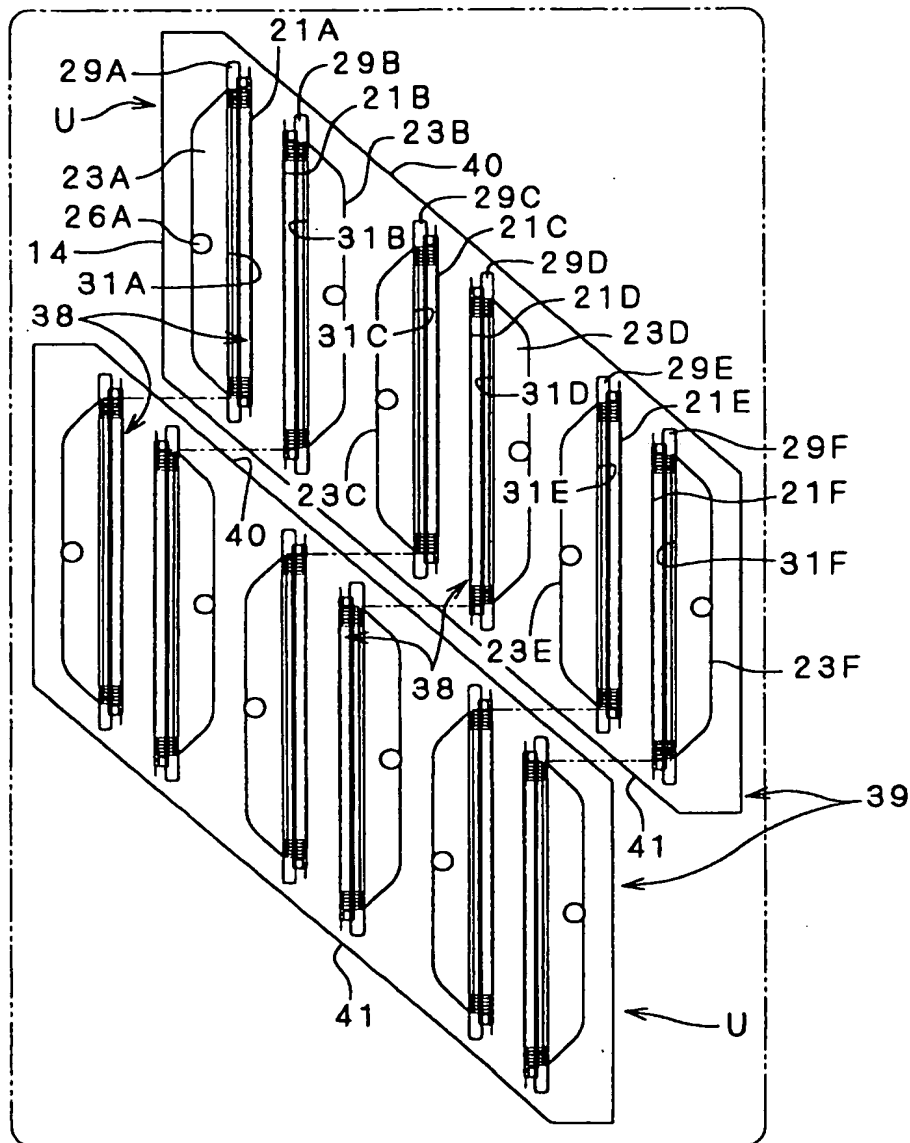
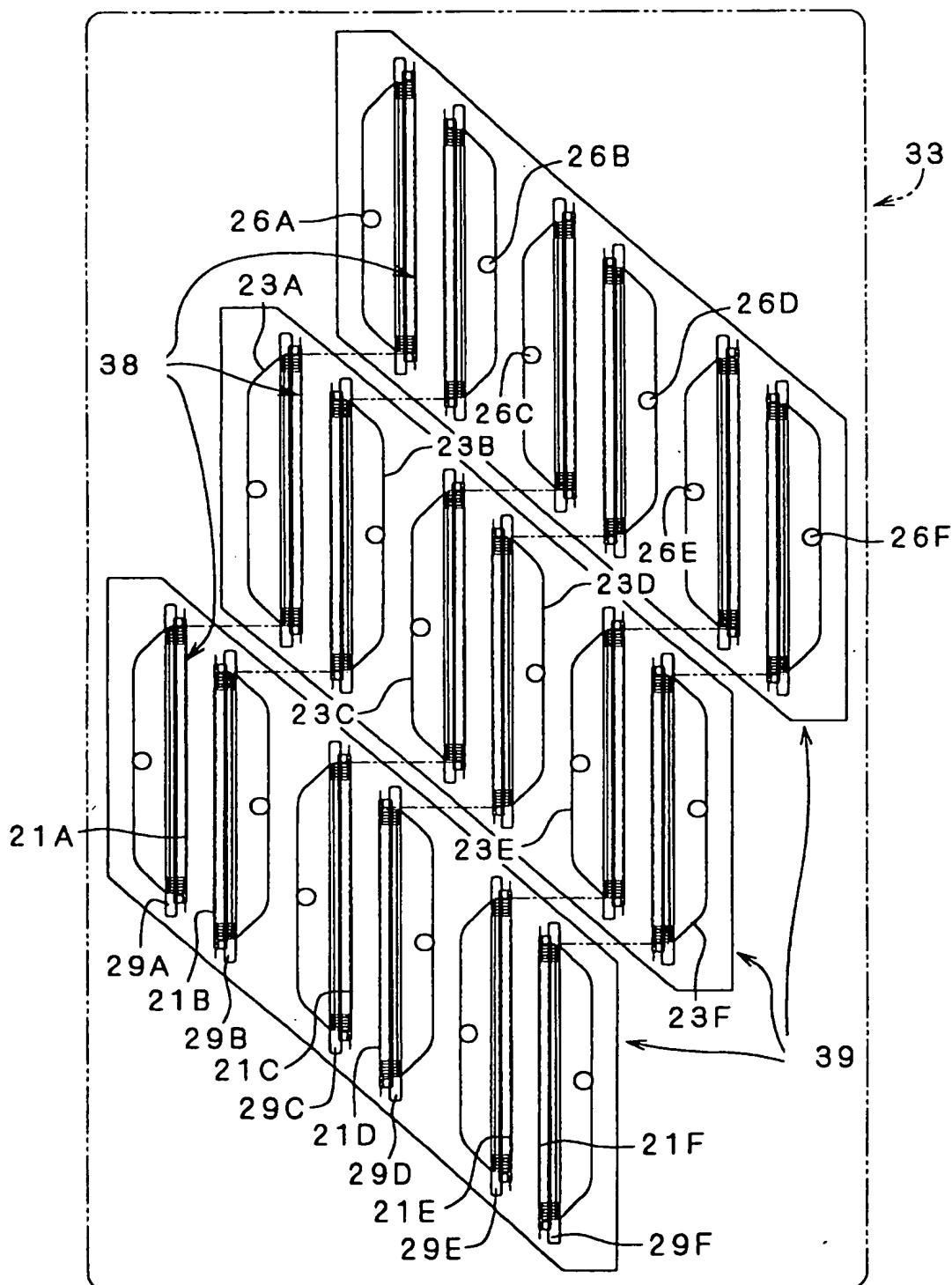


Fig. 8

Fig. 9



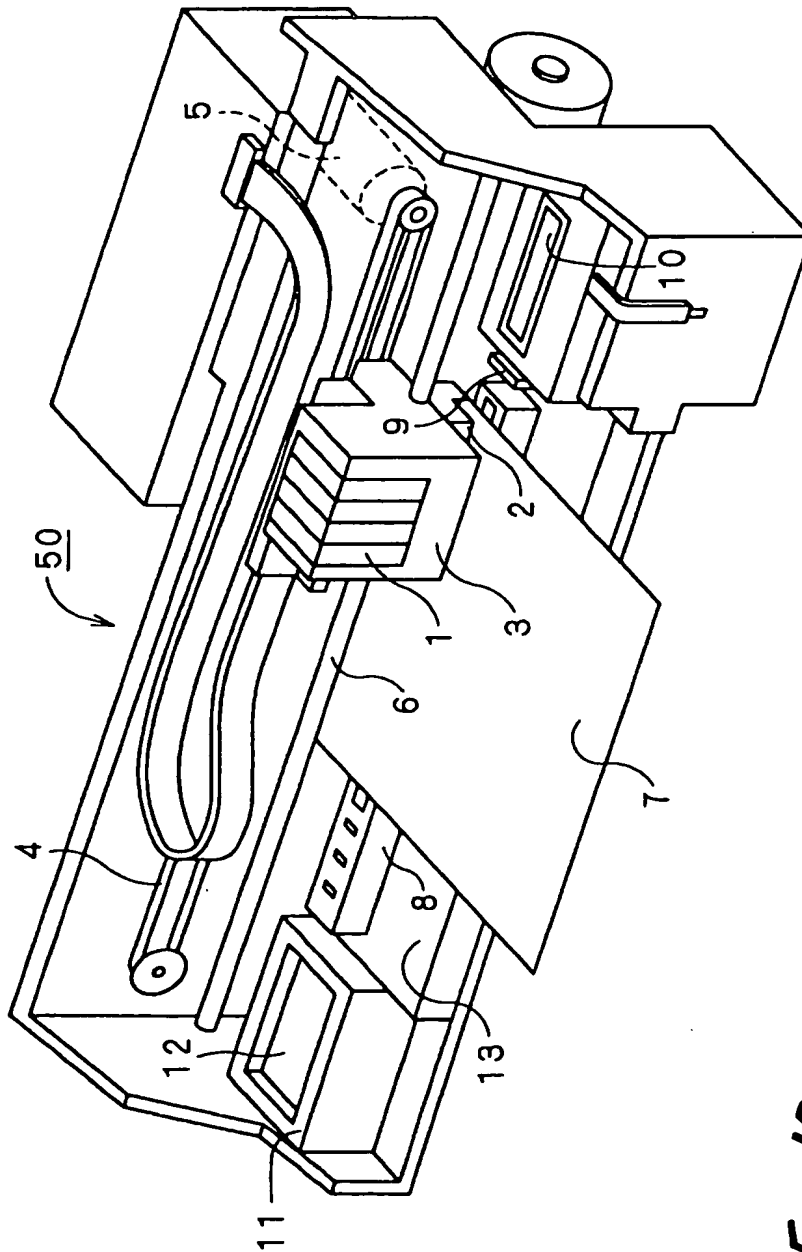


Fig. 10

Fig. 11

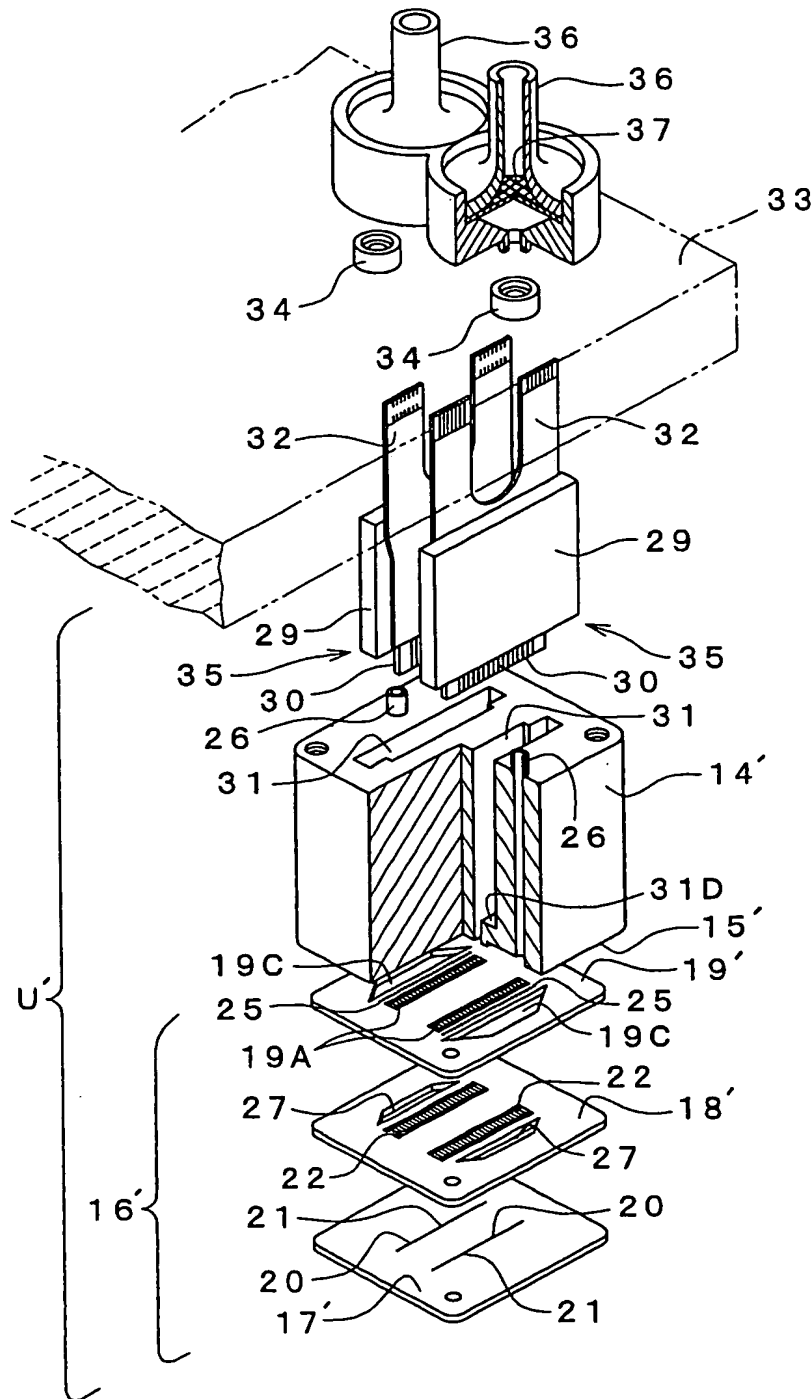


Fig. 12

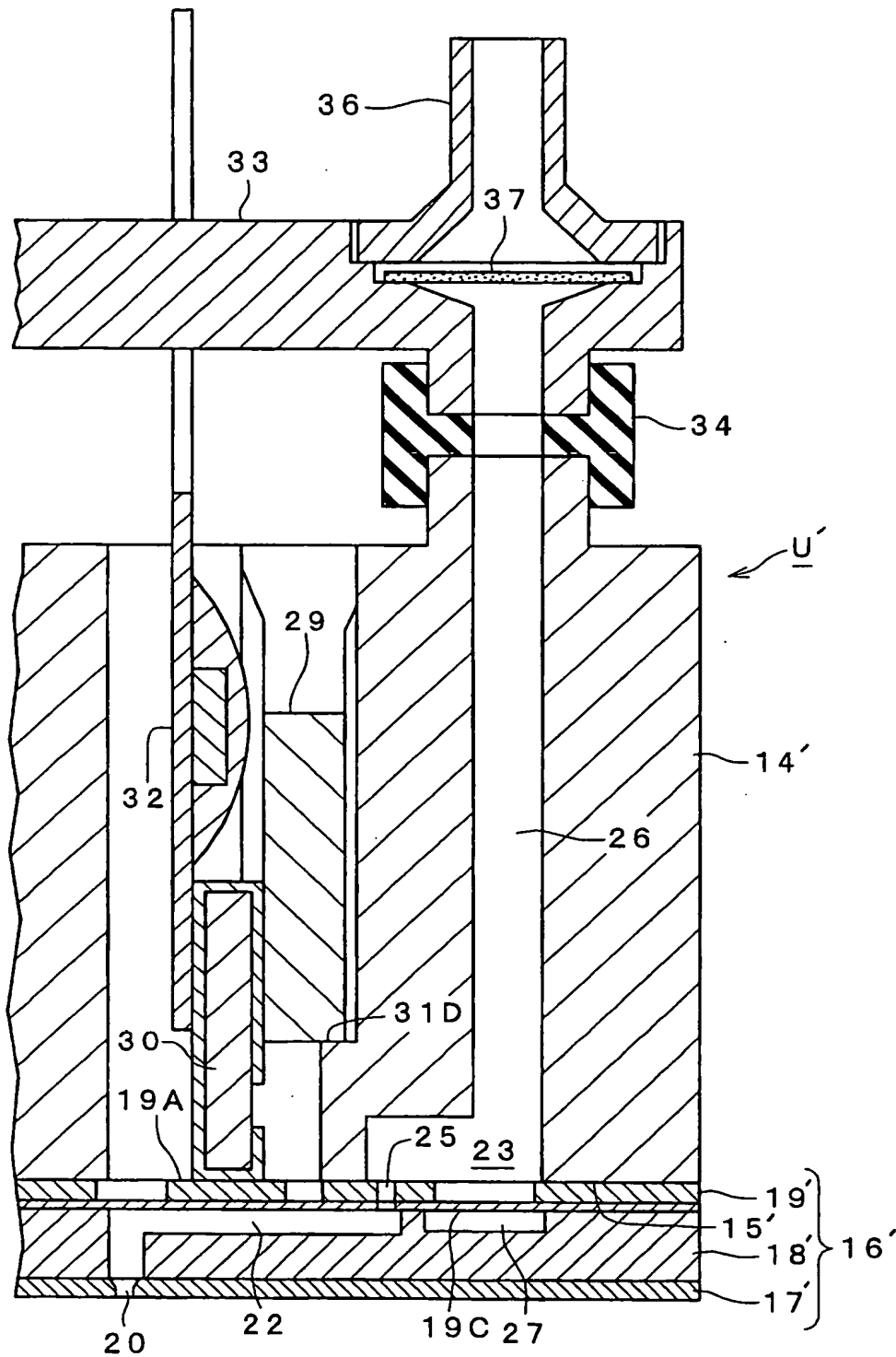


Figure 1 consists of two views of a semiconductor device. The top view is a cross-sectional view showing a stack of layers. From top to bottom, the layers are labeled 31, 32, 31Y, 14', 30, 31, 29, 31X, and 31Z. A force U' is applied to the right side of the device. The bottom view is a plan view showing the same layers. The layers are labeled 20, 21, 32, 30, 17', 29, 31, and 14'. A dimension $L/2$ is indicated for the width of the device. A force U' is applied to the bottom of the device.

Fig. 1 is a perspective view of a rectangular frame assembly 17'. The assembly includes three vertical members 21 and a base 33. The frame is shown in a perspective view with a wavy line indicating a cross-section. Dimensions U and L are indicated.

Fig. 13C

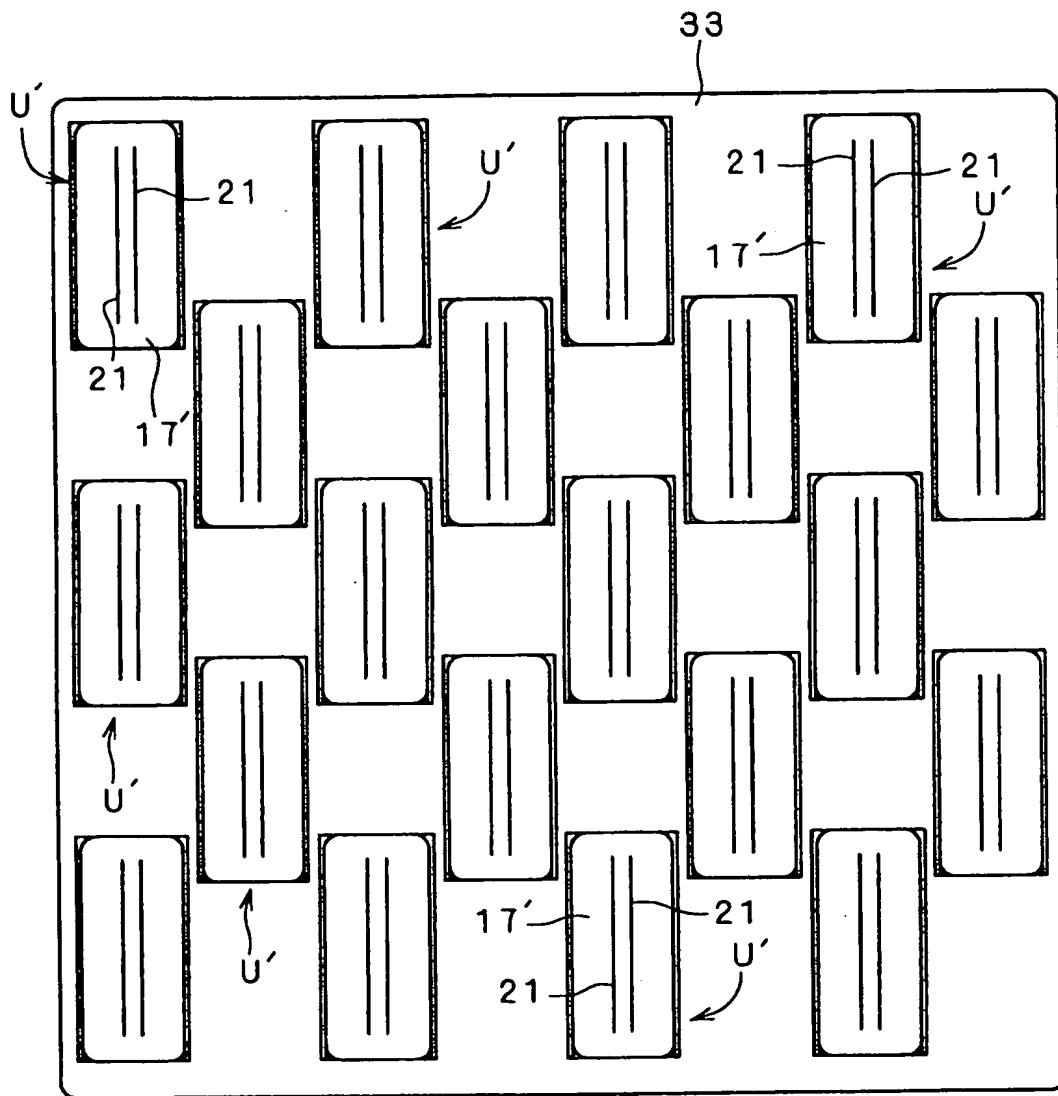


Fig. 14